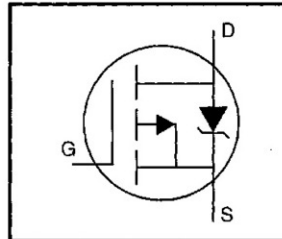


IRF9640PbF

HEXFET® Power MOSFET

- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- P-Channel
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead-Free



$$V_{DSS} = -200V$$

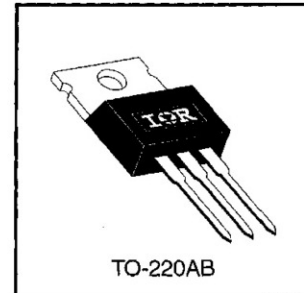
$$R_{DS(on)} = 0.50\Omega$$

$$I_D = -11A$$

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-220 package is universally preferred for all commercial-industrial applications at power dissipation levels to approximately 50 watts. The low thermal resistance and low package cost of the TO-220 contribute to its wide acceptance throughout the industry.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10 V	-11	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ -10 V	-6.8	
I_{DM}	Pulsed Drain Current ①	-44	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	125	W
	Linear Derating Factor	1.0	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	700	mJ
I_{AR}	Avalanche Current ①	-11	A
E_{AR}	Repetitive Avalanche Energy ①	13	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-5.0	V/ns
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	1.0	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.50	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	

IRF9640PbF

International
IR Rectifier

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-200	—	—	V	$V_{GS}=0V$, $I_D=-250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.20	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D=-1mA$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.50	Ω	$V_{GS}=-10V$, $I_D=-6.6A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-2.0	—	-4.0	V	$V_{DS}=V_{GS}$, $I_D=-250\mu A$
g_{fs}	Forward Transconductance	4.1	—	—	S	$V_{DS}=-50V$, $I_D=-6.6A$ ④
I_{DSS}	Drain-to-Source Leakage Current	—	—	-100	μA	$V_{DS}=-200V$, $V_{GS}=0V$
		—	—	-500		$V_{DS}=-160V$, $V_{GS}=0V$, $T_J=125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS}=-20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS}=20V$
Q_g	Total Gate Charge	—	—	44	nC	$I_D=-11A$
Q_{gs}	Gate-to-Source Charge	—	—	7.1		$V_{DS}=-160V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	27		$V_{GS}=-10V$ See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD}=-100V$ $I_D=-11A$ $R_G=9.1\Omega$ $R_D=8.6\Omega$ See Figure 10 ④
t_r	Rise Time	—	43	—		
$t_{d(off)}$	Turn-Off Delay Time	—	39	—		
t_f	Fall Time	—	38	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	1200	—	pF	$V_{GS}=0V$
C_{oss}	Output Capacitance	—	370	—		$V_{DS}=-25V$
C_{rss}	Reverse Transfer Capacitance	—	81	—		$f=1.0MHz$ See Figure 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-11	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-44		
V_{SD}	Diode Forward Voltage	—	—	-5.0	V	$T_J=25^\circ\text{C}$, $I_S=-11A$, $V_{GS}=0V$ ④
t_{rr}	Reverse Recovery Time	—	250	300	ns	$T_J=25^\circ\text{C}$, $I_F=-11A$
Q_{rr}	Reverse Recovery Charge	—	2.9	3.6	μC	$di/dt=100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)

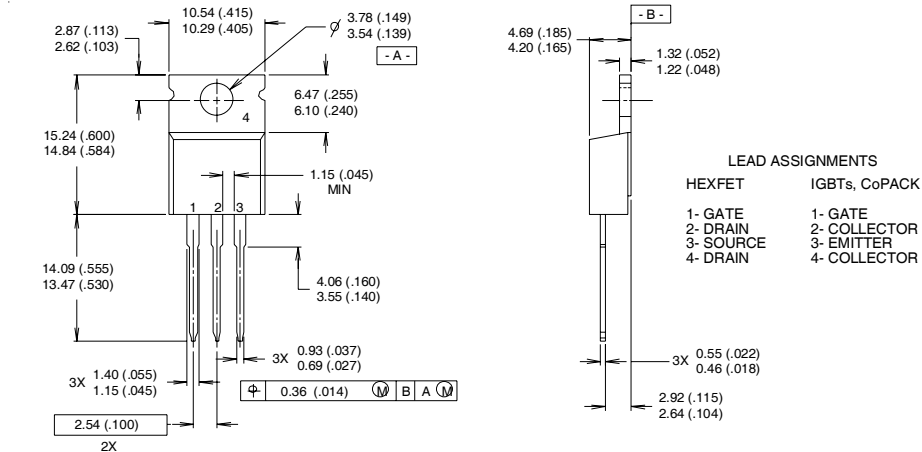
② $V_{DD}=-50V$, starting $T_J=25^\circ\text{C}$, $L=8.7mH$
 $R_G=25\Omega$, $I_{AS}=-11A$ (See Figure 12)

③ $I_{SD}\leq -11A$, $di/dt\leq 150A/\mu s$, $V_{DD}\leq V_{(BR)DSS}$,
 $T_J\leq 150^\circ\text{C}$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982. 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
2 CONTROLLING DIMENSION : INCH 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

